



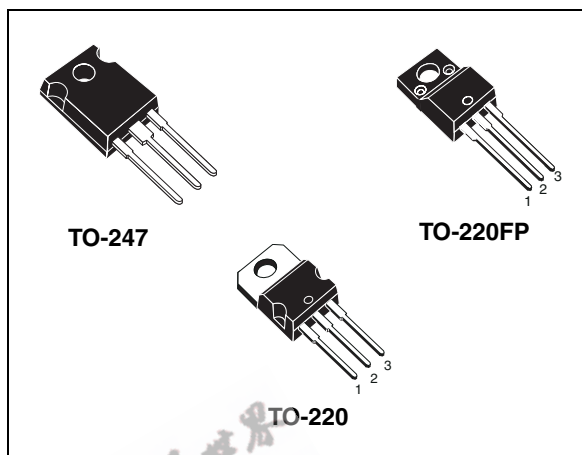
# STF20NM60D - STP20NM60FD STW20NM60FD

N-channel 600V - 0.26Ω - 20A - TO-220 - TO-220FP - TO-247  
FDmesh™ Power MOSFET (with fast diode)

## General features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>	P <sub>w</sub>
STF20NM60D	600V	<0.29Ω	20A	192W
STP20NM60FD	600V	<0.29Ω	20A	45W
STW20NM60FD	600V	<0.29Ω	20A	214W

- High dv/dt and avalanche capabilities
- 100% Avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Tight process control and high manufacturing yields



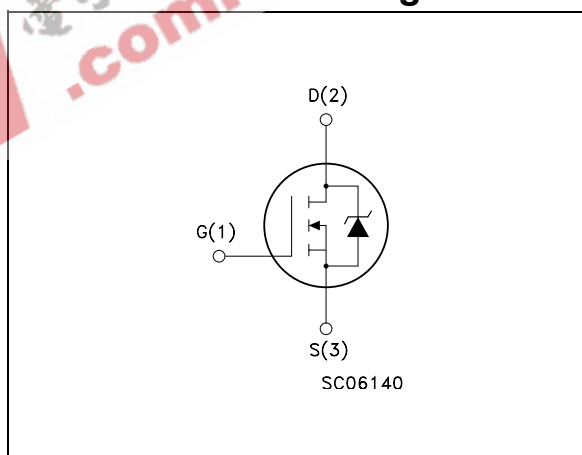
## Description

The FDmesh™ associates all advantages of reduced on-resistance and fast switching with an intrinsic fast-recovery body diode. It is therefore strongly recommended for bridge topologies, in particular ZVS phase-shift converters.

## Applications

- Switching application

## Internal schematic diagram



## Order codes

Part number	Marking	Package	Packaging
STF20NM60D	F20NM60D	TO-220FP	Tube
STP20NM60FD	P20NM60FD	TO-220	Tube
STW20NM60FD	W20NM60FD	TO-247	Tube

# Contents

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# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value			Unit
		TO-220	TO-220FP	TO-247	
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	600			V
$V_{DGR}$	Drain-gate voltage ( $R_{GS} = 20\text{ k}\Omega$ )	600			V
$V_{GS}$	Gate- source voltage	$\pm 30$			V
$I_D$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	20	20 <sup>(1)</sup>	20	A
$I_D$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	12.6	12.6 <sup>(1)</sup>	12.6	A
$I_{DM}^{(2)}$	Drain current (pulsed)	80	80 <sup>(1)</sup>	80	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	192	45	214	W
	Derating factor	1.20	0.36	1.42	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	20			V/ns
$V_{ISO}$	Insulation withstand voltage (DC)	-	2500	-	V
$T_j$	Operating junction temperature	- 65 to 150			$^\circ\text{C}$
$T_{stg}$	Storage temperature				$^\circ\text{C}$

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- $I_{SD} \leq 20\text{A}$ ,  $di/dt \leq 400\text{A}/\mu\text{s}$ ,  $V_{DD} = 80\%V_{(BR)DSS}$

**Table 2. Thermal resistance**

Symbol	Parameter	Value			Unit
		TO-220	TO-220FP	TO-247	
$R_{thj-case}$	Thermal resistance junction-case Max	0.65	2.8	0.585	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient Max	62.5		30	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300			$^\circ\text{C}$

**Table 3. Avalanche data**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	10	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 35\text{ V}$ )	700	mJ

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu A, V_{GS} = 0$	600			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}, T_C = 125^{\circ}C$			1 10	$\mu A$ $\mu A$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 30V$			$\pm 10$ 0	$\mu A$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 10A$		0.26	0.29	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max},$ $I_D = 10A$		9		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$		1300 500 35		pF pF pF
$C_{oss eq.}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 480V$		190		pF
$R_G$	Gate input resistance	$f=1 \text{ MHz}$ Gate DC Bias = 0 Test signal level = 20mV open drain		2.7		$\Omega$
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480V, I_D = 20A,$ $V_{GS} = 10V$ (see Figure 17)		37 10 17	52	nC nC nC

1. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %
2.  $C_{oss eq.}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD} = 300V, I_D = 10A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 16)		25 12		ns ns
$t_{r(Voff)}$ $t_f$ $t_c$	Off-voltage rise time Fall time Cross-over time	$V_{DD} = 480V, I_D = 20A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 16)		8 22 30		ns ns ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				20 80	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 20A, V_{GS} = 0$			1.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 20A, T_j = 25^\circ C$ $di/dt = 100A/\mu s, V_{DD} = 60V$ (see Figure 21)		240 1800 16		ns nC A
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 20A, T_j = 150^\circ C$ $di/dt = 100A/\mu s, V_{DD} = 60V$ (see Figure 21)		396 2960 20		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220

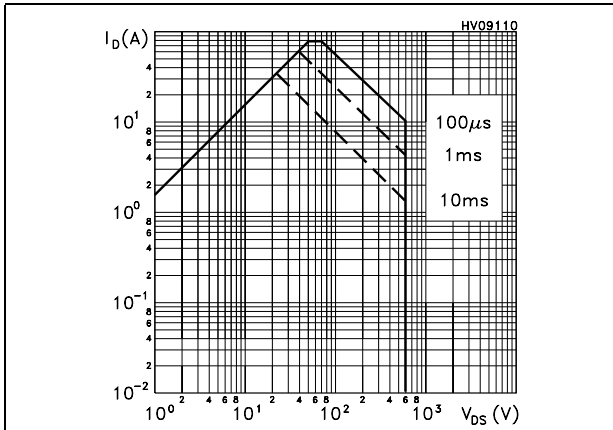


Figure 2. Thermal impedance for TO-220

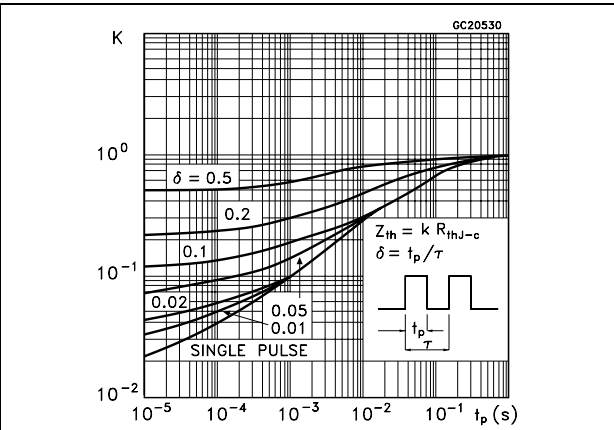


Figure 3. Safe operating area for TO-220FP

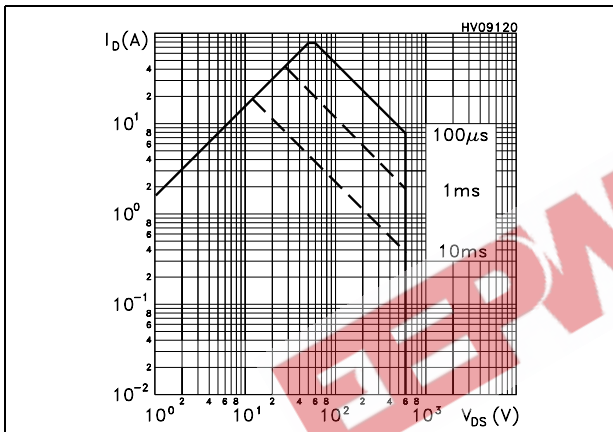


Figure 4. Thermal impedance for TO-220FP

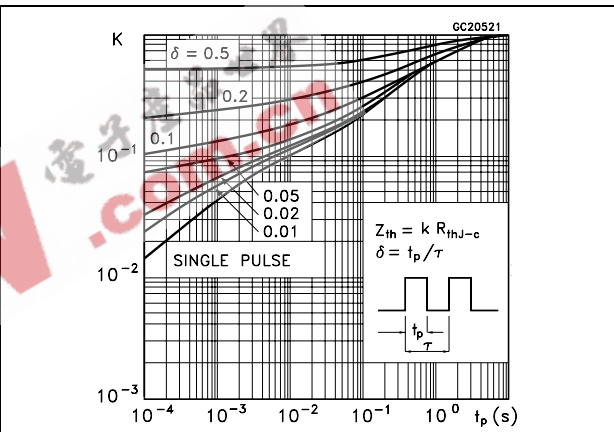


Figure 5. Safe operating area for TO-247

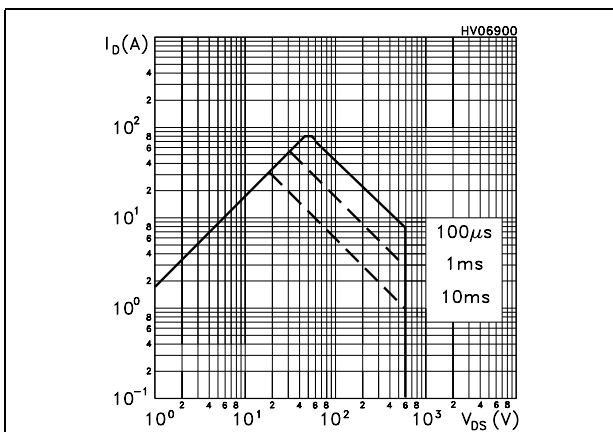


Figure 6. Thermal impedance for TO-247

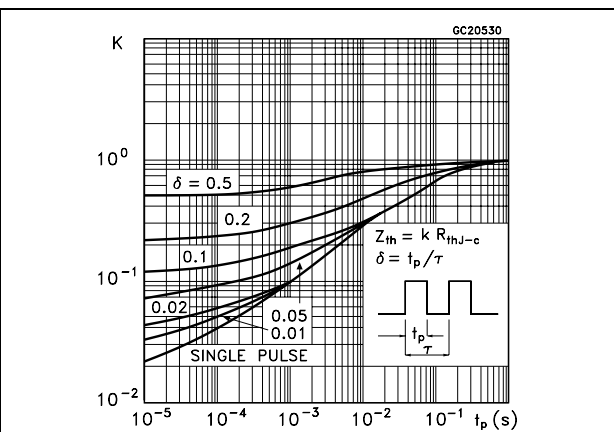


Figure 7. Output characteristics

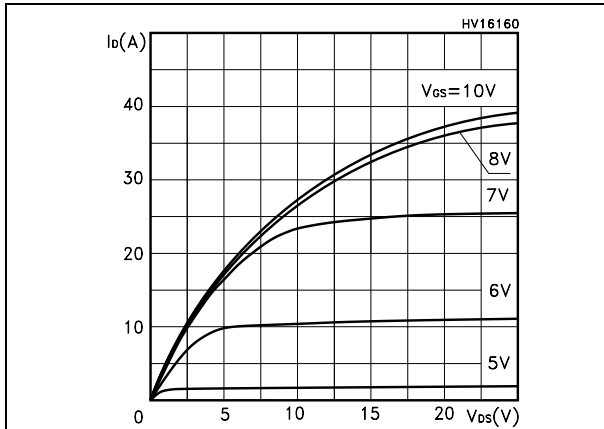


Figure 8. Transfer characteristics

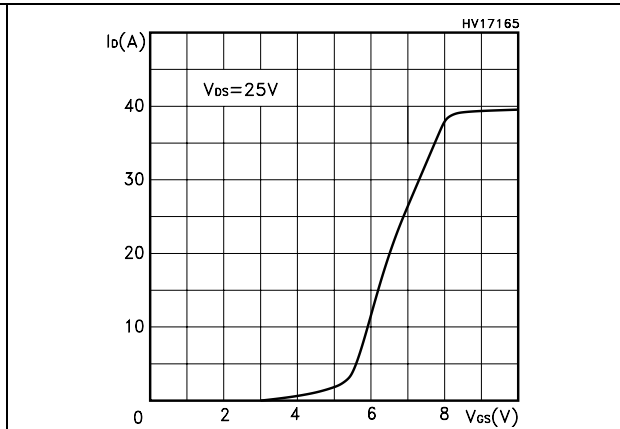


Figure 9. Transconductance

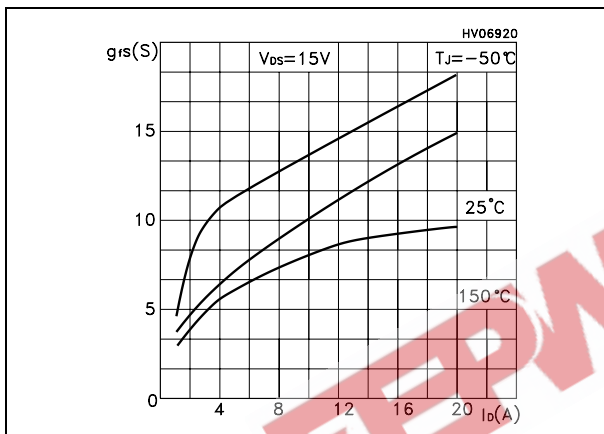


Figure 10. Static drain-source on resistance

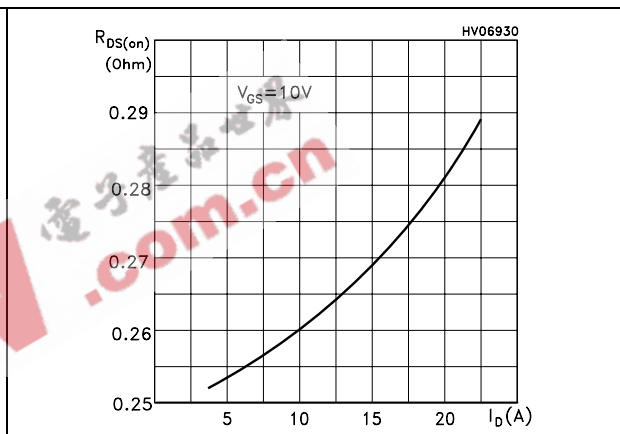


Figure 11. Gate charge vs gate-source voltage Figure 12. Capacitance variations

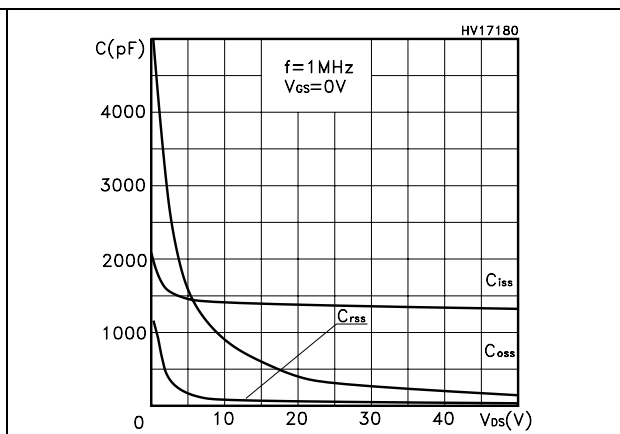
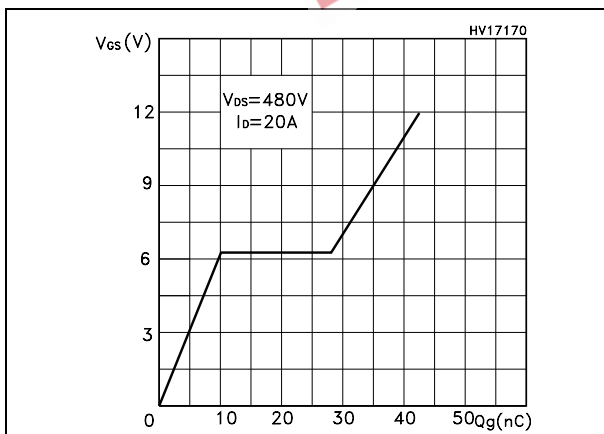


Figure 13. Normalized gate threshold voltage vs temperature

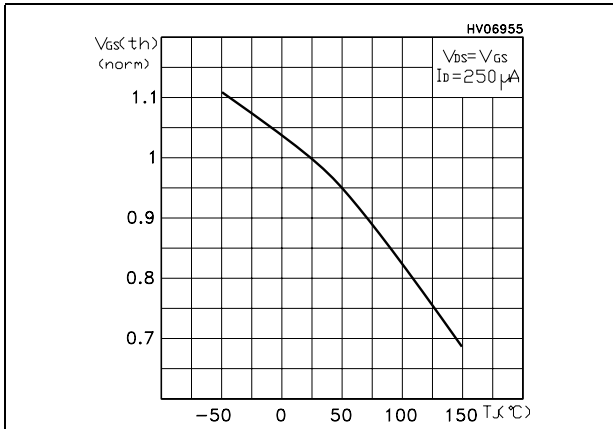


Figure 14. Normalized on resistance vs temperature

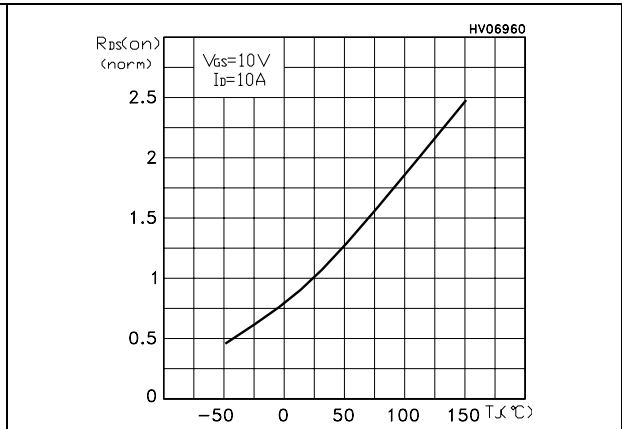
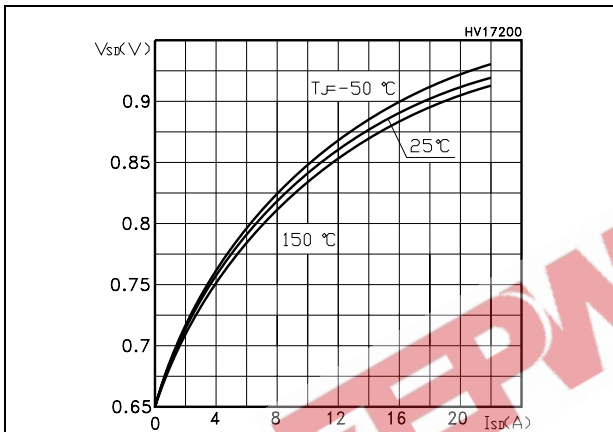


Figure 15. Source-drain diode forward characteristics





### 3 Test circuit

Figure 16. Switching times test circuit for resistive load

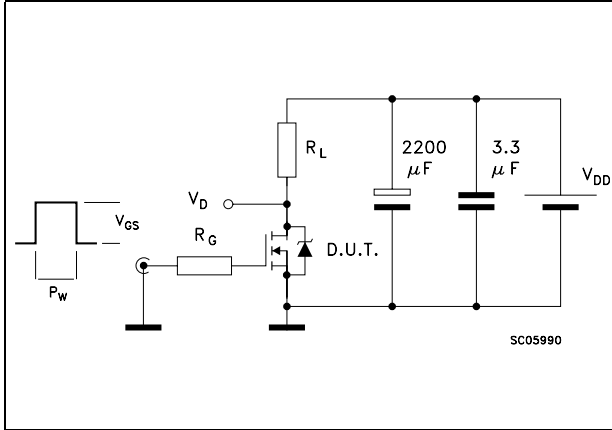


Figure 17. Gate charge test circuit

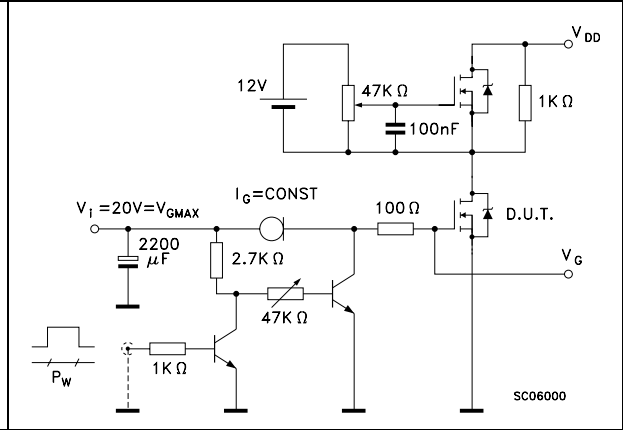


Figure 18. Test circuit for inductive load switching and diode recovery times

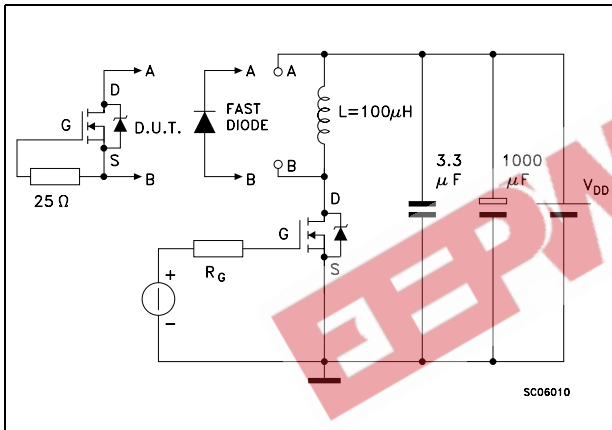


Figure 19. Unclamped inductive load test circuit

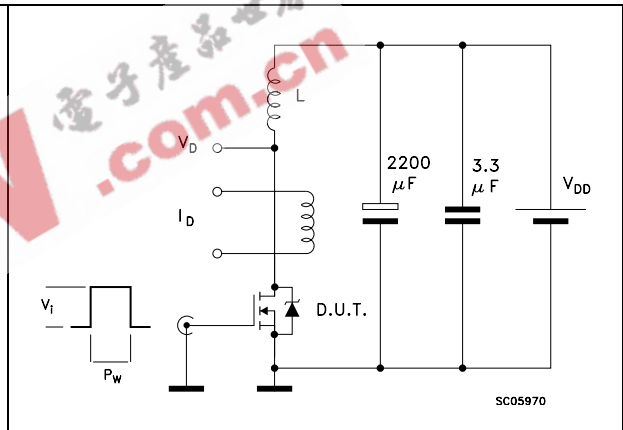


Figure 20. Unclamped inductive waveform

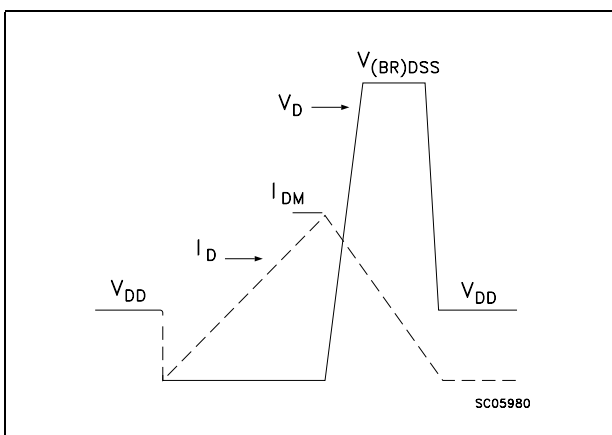
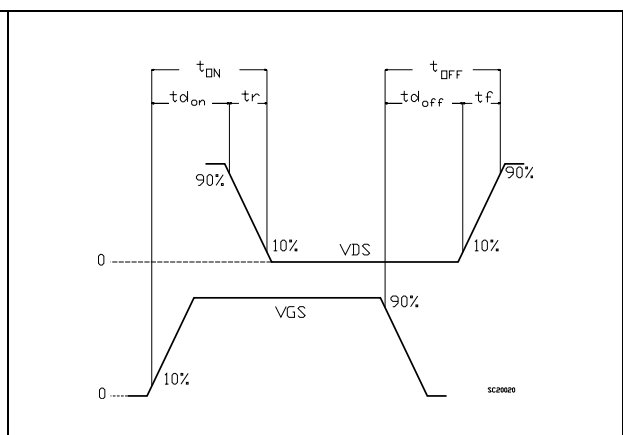


Figure 21. Switching time waveform



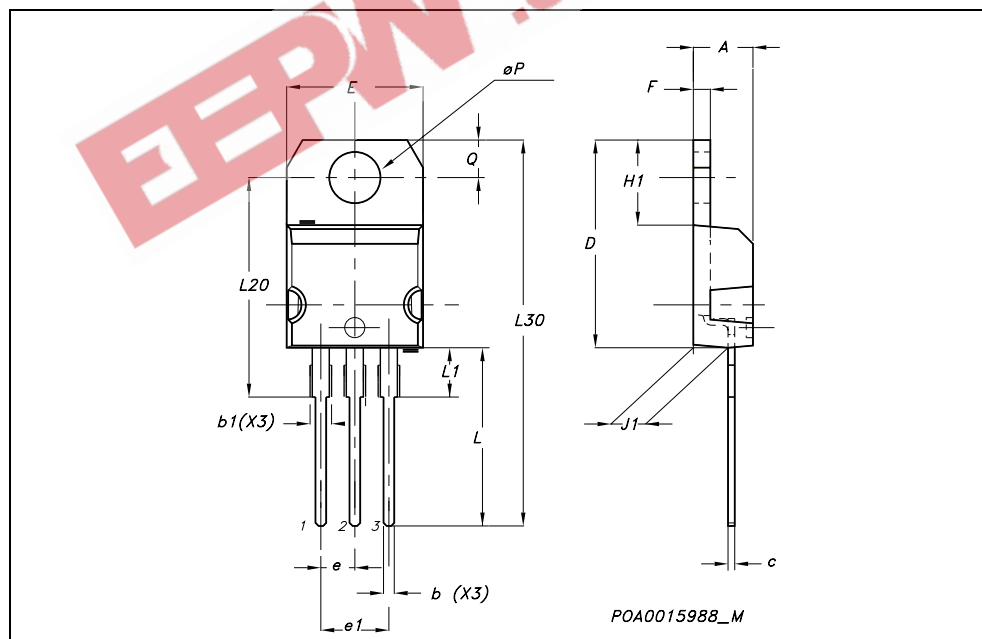
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : [www.st.com](http://www.st.com)

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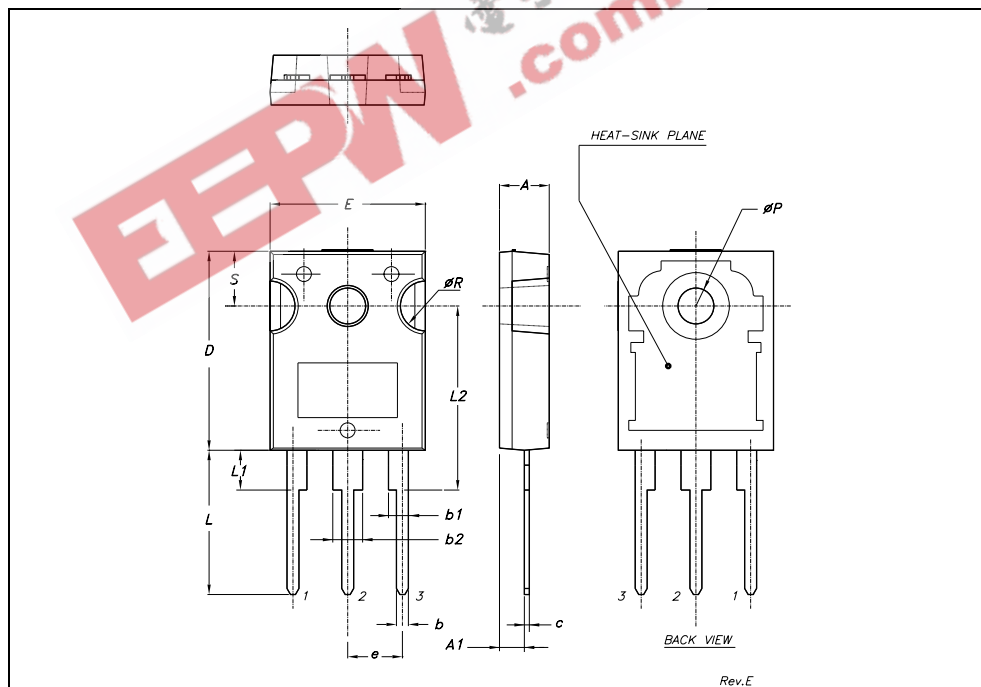
## TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



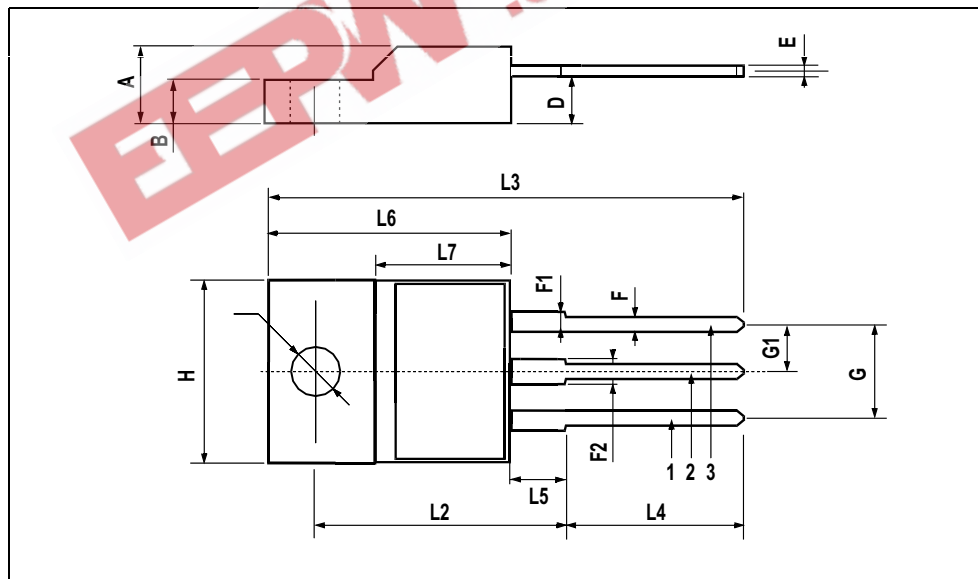
**TO-247 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



## TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



## 5 Revision history

Table 8. Revision history

Date	Revision	Changes
09-Sep-2004	1	First release
21-Apr-2006	2	New template
25-Jul-2006	3	Modified part number
01-Aug-2006	4	Corrected unit on <a href="#">Table 5.: Dynamic</a>

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